Bi-Directional P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{S1S2} (V)	$R_{S1S2(on)}$ (Ω)	I_{S1S2} (A)
- 20	0.060 at V_{GS} = - 4.5 V	- 4.4
	0.080 at V_{GS} = - 2.5 V	- 3.9
	0.105 at V_{GS} = - 1.8 V	- 3.4

FEATURES

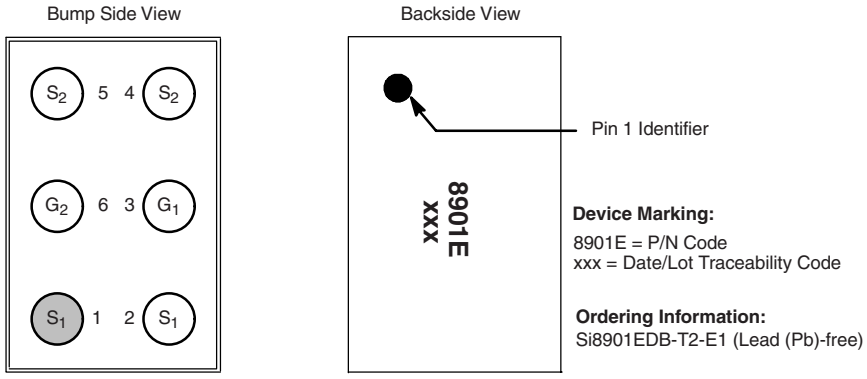
- TrenchFET® Power MOSFET
- Ultra-Low $R_{SS(on)}$
- ESD Protected: 6000 V
- MICRO FOOT® Chipscale Packaging Reduces Footprint Area, Profile (0.65 mm) and On-Resistance Per Footprint Area

Pb-free
RoHS COMPLIANT

APPLICATIONS

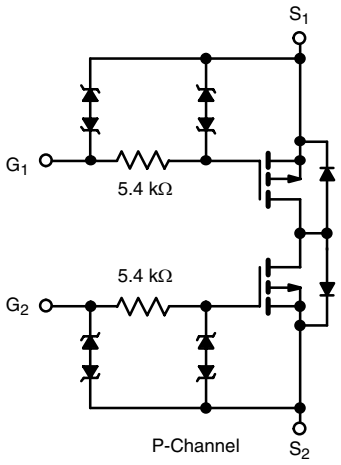
- Smart Batteries for Portable Devices

MICRO FOOT



Device Marking:
8901E = P/N Code
xxx = Date/Lot Traceability Code

Ordering Information:
Si8901EDB-T2-E1 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**5 s**	**Steady State**	**Unit**
Source1- Source2 Voltage		V_{S1S2}	- 20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Source1- Source2 Current (T_J = 150 °C)[a]	T_A = 25 °C	I_{S1S2}	- 4.4	- 3.5	A
	T_A = 85 °C		- 3.2	- 2.5	
Pulsed Source1- Source2 Current		I_{SM}	- 10		
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	1.7	1	W
	T_A = 85 °C		0.8	0.5	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C
Package Reflow Conditions[c]	IR/Convection		260		

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	60	75	°C/W
	Steady State		95	120	
Maximum Junction-to-Foot[b]	Steady State	R_{thJF}	18	22	

Notes:
a. Surface Mounted on 1" x 1" FR4 board.
b. The foot is defined as the top surface of the package.
c. Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{SS} = V_{GS}, I_D = - 350 µA	- 0.45		- 1.0	V
Gate-Body Leakage	I_{GSS}	V_{SS} = 0 V, V_{GS} = ± 4.5 V			± 4	µA
		V_{SS} = 0 V, V_{GS} = ± 12 V			± 10	mA
Zero Gate Voltage Source Current	I_{S1S2}	V_{SS} = - 20 V, V_{GS} = 0 V			- 1	µA
		V_{SS} = - 20 V, V_{GS} = 0 V, T_J = 85 °C			- 5	
On-State Source Current[a]	$I_{S(on)}$	V_{SS} = - 5 V, V_{GS} = - 4.5 V	- 5			A
Source1- Source2 On-State Resistance[a]	$R_{S1S2(on)}$	V_{GS} = - 4.5 V, I_{SS} = - 1 A		0.048	0.060	Ω
		V_{GS} = - 2.5 V, I_{SS} = - 1 A		0.062	0.080	
		V_{GS} = - 1.8 V, I_{SS} = - 1 A		0.081	0.105	
Forward Transconductance[a]	g_{fs}	V_{SS} = - 10 V, I_{SS} = - 1 A		7		S
Dynamic[b]						
Turn-On Delay Time	$t_{d(on)}$	V_{SS} = - 10 V, R_L = 10 Ω I_{SS} ≅ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		2.3	3.5	µs
Rise Time	t_r			2.2	3.5	
Turn-Off Delay Time	$t_{d(off)}$			1.3	2	
Fall Time	t_f			9	14	

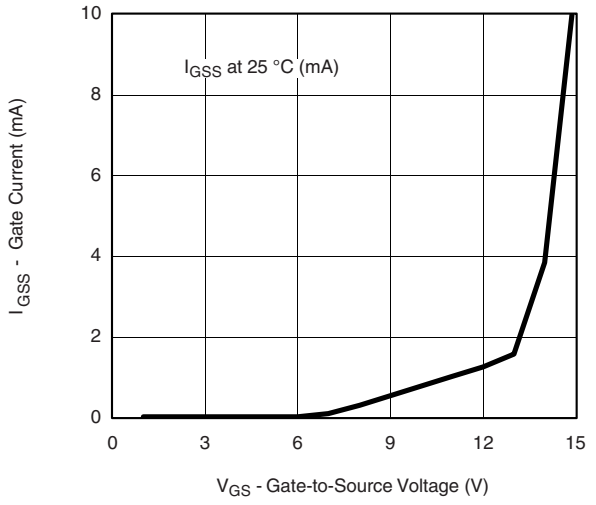
Notes:

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

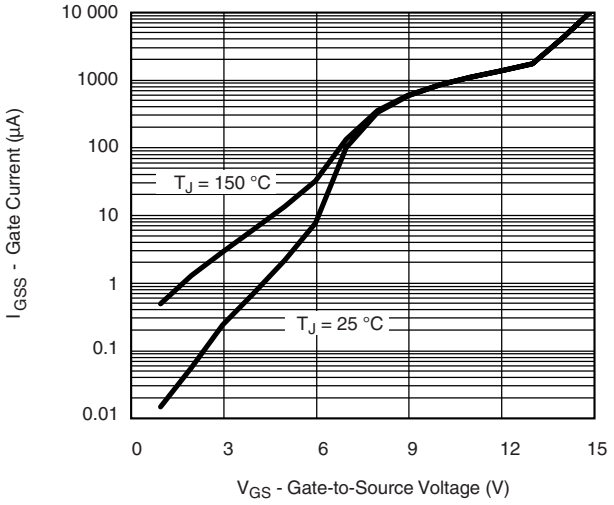
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

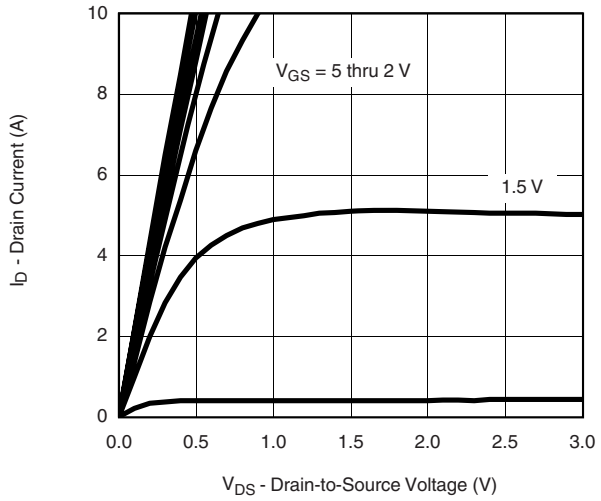


Gate-Current vs. Gate-Source Voltage

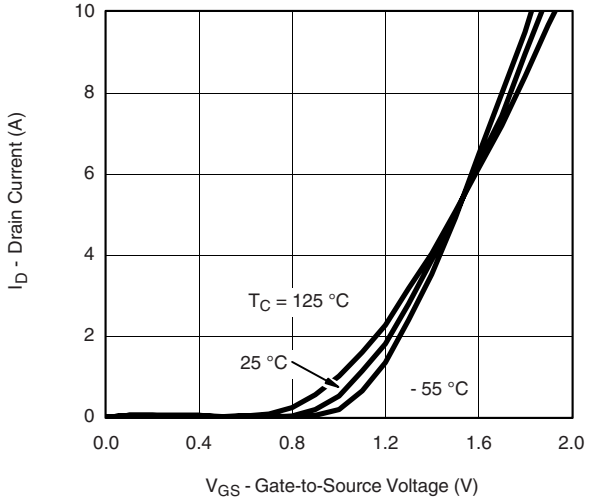


Gate Current vs. Gate-Source Voltage

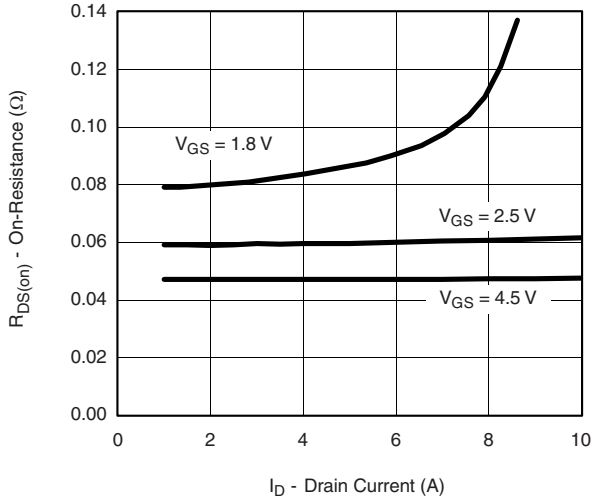
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



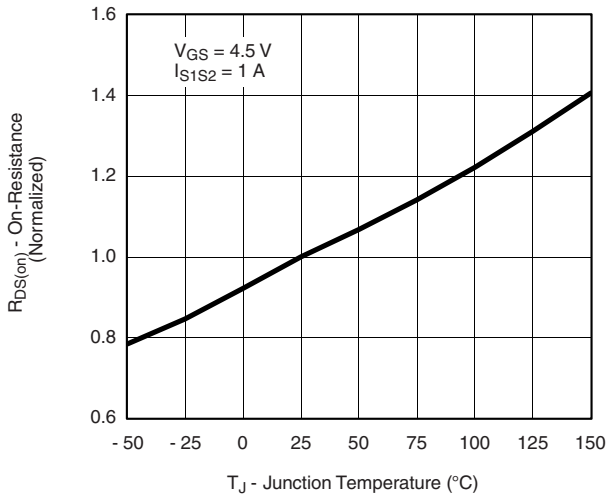
Output Characteristics



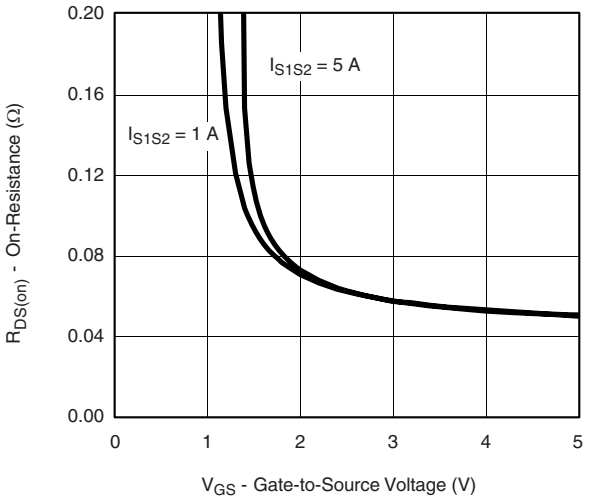
Transfer Characteristics



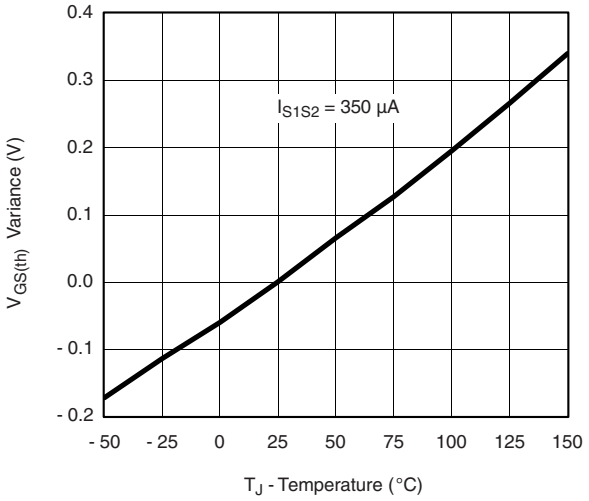
On-Resistance vs. Drain Current



On-Resistance vs. Junction Temperature

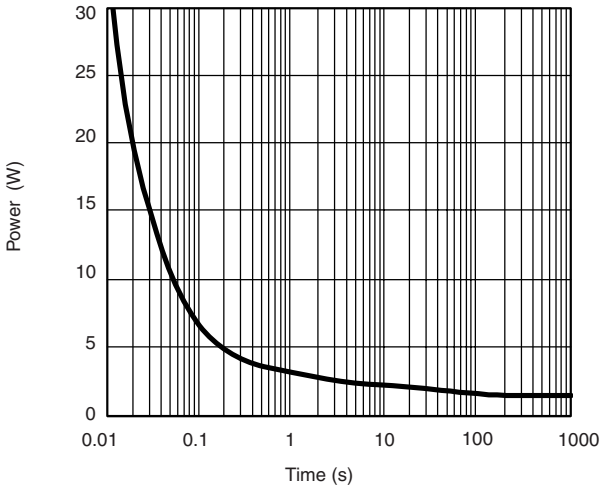


On-Resistance vs. Gate-to-Source Voltage

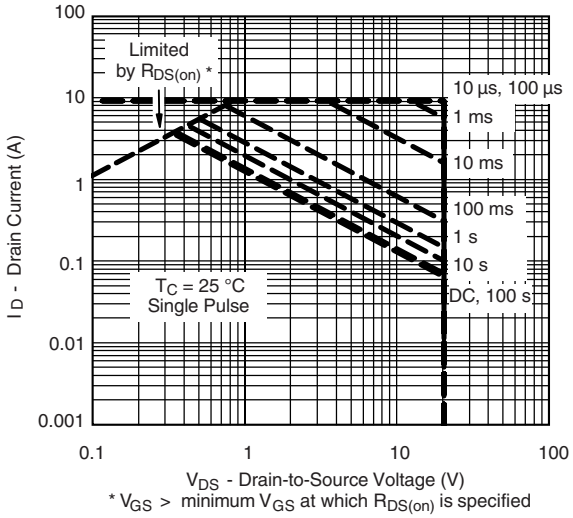


Threshold Voltage

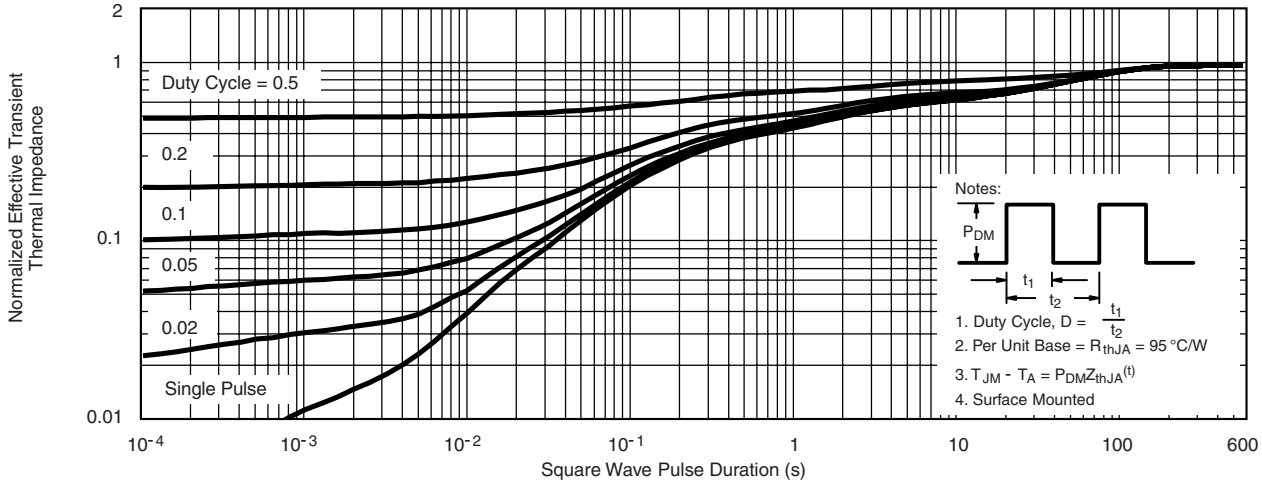
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



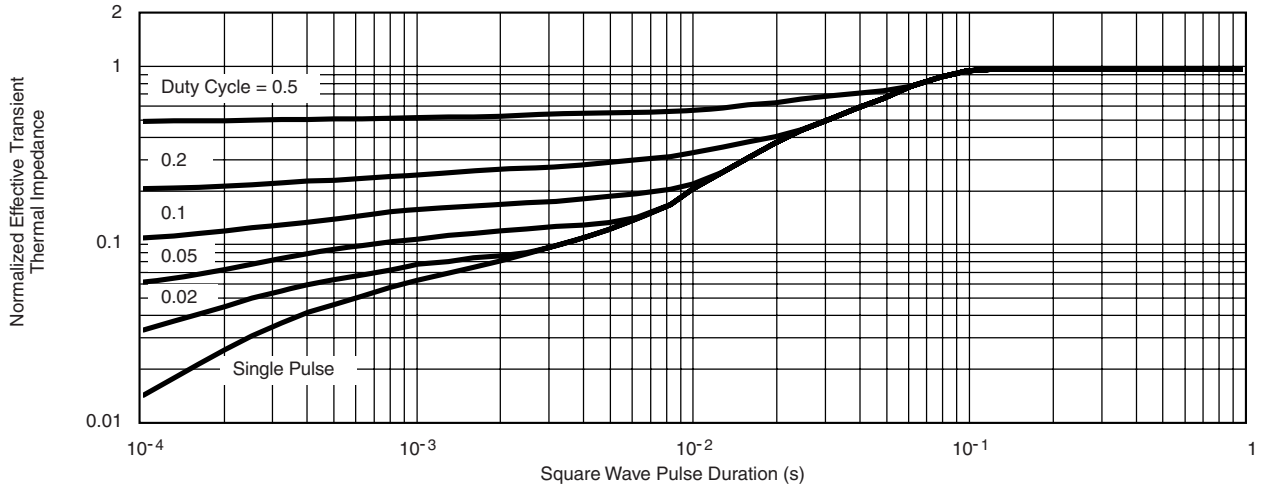
Single Pulse Power, Junction-to-Ambient



Safe Operating Area



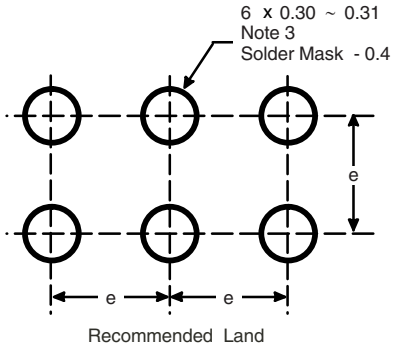
Normalized Thermal Transient Impedance, Junction-to-Ambient

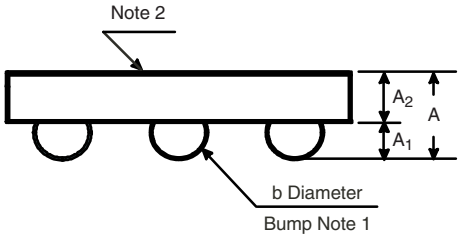


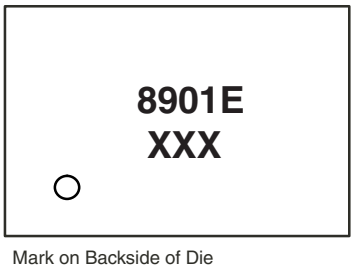
Normalized Thermal Transient Impedance, Junction-to-Foot

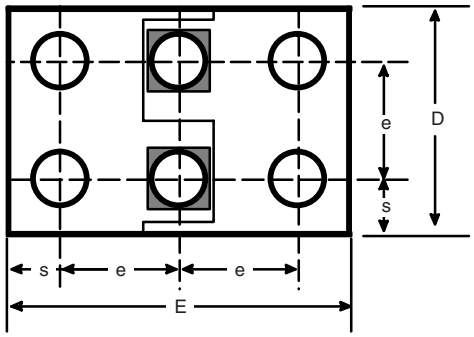
PACKAGE OUTLINE

MICRO FOOT: 6-BUMP (2 x 3, 0.8 mm PITCH)









Notes (Unless Otherwise Specified):
1. 6 solder bumps are 95.5/3.8/0.7 Sn/Ag/Cu.
2. Backside surface is coated with a Ag/Ni/Ti layer.
3. Non-solder mask defined copper landing pad.
4. Laser marks on the silicon die back.

Dim.	Millimeters[a]		Inches	
	Min.	Max.	Min.	Max.
A	0.600	0.650	0.0236	0.0256
A_1	0.260	0.290	0.102	0.114
A_2	0.340	0.360	0.0134	0.0142
b	0.370	0.410	0.0146	0.0161
D	1.52	1.6	0.0598	0.0630
E	2.32	2.4	0.0913	0.0945
e	0.750	0.850	0.0295	0.0335
s	0.380	0.400	0.0150	0.0157

Notes:
a. Use millimeters as the primary measurement.

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